

Wladyslaw

List of Publications by Year in Descending Order

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The third column is the impact factor (IF) of the journal, and the fourth column is the number of citations of the article.

444
papers

20,373
citations

69
h-index

130
g-index

475
ext. papers

21,779
ext. citations

3.3
avg, IF

6.35
L-index

#	Paper	IF	Citations
444	Effect of oxygen flow rate on properties of Cu ₄ O ₃ thin films fabricated by radio frequency magnetron sputtering. <i>Journal of Applied Physics</i> , 2020 , 127, 085302	2.5	7
443	Nitrogen Doping Effect in Cu ₄ O ₃ Thin Films Fabricated by Radio Frequency Magnetron Sputtering. <i>Physica Status Solidi (B): Basic Research</i> , 2020 , 257, 1900363	1.3	4
442	Effects of the host conduction band energy on the electronic band structure of ZnCdTeO dilute oxide alloys. <i>Journal of Applied Physics</i> , 2019 , 126, 083106	2.5	2
441	Amorphous gallium oxide sulfide: A highly mismatched alloy. <i>Journal of Applied Physics</i> , 2019 , 126, 105708	2.5	3
440	ZnO _{1-x} Te _x highly mismatched alloys beyond the dilute alloy limit: Synthesis and electronic band structure. <i>Journal of Applied Physics</i> , 2019 , 125, 155702	2.5	7
439	Cl-doping effect in ZnTe _{1-x} O _x highly mismatched alloys for intermediate band solar cells. <i>Journal of Applied Physics</i> , 2019 , 125, 243109	2.5	4
438	Growth of GaP _{1-x} As _y N _x on Si substrates by chemical beam epitaxy. <i>Journal of Applied Physics</i> , 2019 , 126, 105704	2.5	1
437	Room-Temperature-Synthesized High-Mobility Transparent Amorphous CdO-GaO Alloys with Widely Tunable Electronic Bands. <i>ACS Applied Materials & Interfaces</i> , 2018 , 10, 7239-7247	9.5	11
436	Reconfiguring crystal and electronic structures of MoS ₂ by substitutional doping. <i>Nature Communications</i> , 2018 , 9, 199	17.4	85
435	Improved photovoltaic properties of ZnTeO-based intermediate band solar cells 2018 ,		2
434	Engineering Electronic Band Structure of Indium-doped Cd _{1-x} Mg _x O Alloys for Solar Power Conversion Applications. <i>Energy Technology</i> , 2018 , 6, 122-126	3.5	4
433	Bistable Amphoteric Native Defect Model of Perovskite Photovoltaics. <i>Journal of Physical Chemistry Letters</i> , 2018 , 9, 3878-3885	6.4	11
432	Carrier Lifetimes in a III-V Intermediate-Band Semiconductor. <i>Physical Review Applied</i> , 2017 , 7,	4.3	5
431	Growth and characterization of Zn _{1-x} Cd _x Te _{1-y} O _y highly mismatched alloys for intermediate band solar cells. <i>Solar Energy Materials and Solar Cells</i> , 2017 , 169, 1-7	6.4	6
430	. <i>IEEE Journal of Photovoltaics</i> , 2017 , 7, 1024-1030	3.7	9
429	Multicolor emission from intermediate band semiconductor ZnOSe. <i>Scientific Reports</i> , 2017 , 7, 44214	4.9	11
428	Effects of band anticrossing on the temperature dependence of the band gap of ZnSe _{1-x} O _x alloys. <i>Semiconductor Science and Technology</i> , 2017 , 32, 015005	1.8	5

427	On the thermal degradation of tunnel diodes in multijunction solar cells 2017 ,		7
426	Effects of Ni d-levels on the electronic band structure of $\text{Ni}_x\text{Cd}_{1-x}\text{O}$ semiconducting alloys. <i>Journal of Applied Physics</i> , 2017 , 122, 185703	2.5	9
425	Nitrogen-related intermediate band in P-rich GaNPAs alloys. <i>Scientific Reports</i> , 2017 , 7, 15703	4.9	11
424	On the Use of Transparent Conductive Oxides in High Concentrator III-V Multijunction Solar Cells 2017 ,		1
423	Intermixing studies in $\text{GaN}_{1-x}\text{Sb}_x$ highly mismatched alloys. <i>Applied Optics</i> , 2017 , 56, B64-B69	0.2	3
422	Highly mismatched $\text{GaN}_{1-x}\text{Sb}_x$ alloys: synthesis, structure and electronic properties. <i>Semiconductor Science and Technology</i> , 2016 , 31, 083001	1.8	13
421	Multicolor Electroluminescence from Intermediate Band Solar Cell Structures. <i>Advanced Energy Materials</i> , 2016 , 6, 1501820	21.8	10
420	Compositional dependence of optical transition energies in highly mismatched $\text{Zn}_{1-x}\text{Cd}_x\text{Te}_{1-y}\text{O}_y$ alloys. <i>Applied Physics Express</i> , 2016 , 9, 021202	2.4	5
419	Pressure-induced structural transition of $\text{Cd}_x\text{Zn}_{1-x}\text{O}$ alloys. <i>Applied Physics Letters</i> , 2016 , 108, 152105	3.4	9
418	Undoped p-type $\text{GaN}_{1-x}\text{Sb}_x$ alloys: Effects of annealing. <i>Applied Physics Letters</i> , 2016 , 109, 252102	3.4	5
417	Defects and properties of cadmium oxide based transparent conductors. <i>Journal of Applied Physics</i> , 2016 , 119, 181501	2.5	26
416	Effects of Free Carriers on the Optical Properties of Doped CdO for Full-Spectrum Photovoltaics. <i>Physical Review Applied</i> , 2016 , 6,	4.3	41
415	Semiempirical modeling of a three sublayer photoanode for highly efficient photoelectrochemical water splitting: Parameter and electrolyte optimizations. <i>Solar Energy Materials and Solar Cells</i> , 2016 , 157, 190-199	6.4	3
414	Formation of Nanoscale Composites of Compound Semiconductors Driven by Charge Transfer. <i>Nano Letters</i> , 2016 , 16, 5247-54	11.5	9
413	Effects of a semiconductor matrix on the band anticrossing in dilute group II-VI oxides. <i>Semiconductor Science and Technology</i> , 2015 , 30, 085018	1.8	14
412	InGaN pn-junctions grown by PA-MBE: Material characterization and fabrication of nanocolumn electroluminescent devices. <i>Journal of Crystal Growth</i> , 2015 , 425, 393-397	1.6	7
411	. <i>IEEE Journal of Photovoltaics</i> , 2015 , 5, 878-884	3.7	5
410	Effects of native defects on properties of low temperature grown, non-stoichiometric gallium nitride. <i>Journal Physics D: Applied Physics</i> , 2015 , 48, 385101	3	5

409	Exploration of the growth parameter space for MBE-grown GaN _{1-x} Bb highly mismatched alloys. <i>Journal of Crystal Growth</i> , 2015 , 425, 255-257	1.6	8
408	Temperature evolution of carrier dynamics in GaN _x PyAs _{1-y} alloys. <i>Journal of Applied Physics</i> , 2015 , 117, 175702	2.5	15
407	Effects of the d-donor level of vanadium on the properties of Zn _{1-x} VxO films. <i>Applied Physics Letters</i> , 2015 , 106, 182101	3.4	9
406	Indium doped Cd _{1-x} ZnxO alloys as wide window transparent conductors. <i>Thin Solid Films</i> , 2015 , 597, 183-187	2.2	6
405	Growth and characterization of highly mismatched Zn _{1-x} CdxTe _{1-y} Oy alloys for intermediate band solar cells 2015 ,		1
404	Evidence of extreme type-III band offset at buried n-type CdO/p-type SnTe interfaces. <i>Physical Review B</i> , 2015 , 91,	3.3	7
403	Growth and characterization of ZnO _{1-x} Sx highly mismatched alloys over the entire composition. <i>Journal of Applied Physics</i> , 2015 , 118, 215702	2.5	36
402	Fabrication and characterization of multiband solar cells based on highly mismatched alloys. <i>Journal of Physics: Conference Series</i> , 2015 , 647, 012067	0.3	
401	Simultaneous Enhancement of Electrical Conductivity and Thermopower of Bi ₂ Te ₃ by Multifunctionality of Native Defects. <i>Advanced Materials</i> , 2015 , 27, 3681-6	24	79
400	Electronic band structure of ZnO-rich highly mismatched ZnO _{1-x} Tex alloys. <i>Applied Physics Letters</i> , 2015 , 106, 092101	3.4	24
399	NixCd _{1-x} O: Semiconducting alloys with extreme type III band offsets. <i>Applied Physics Letters</i> , 2015 , 106, 022110	3.4	16
398	Fermi-level stabilization in the topological insulators Bi ₂ Se ₃ and Bi ₂ Te ₃ : Origin of the surface electron gas. <i>Physical Review B</i> , 2014 , 89,	3.3	39
397	Modeling of the atomic structure and electronic properties of amorphous GaN _{1-x} Asx. <i>Computational Materials Science</i> , 2014 , 82, 100-106	3.2	12
396	Growth and characterization of highly mismatched GaN _{1-x} Sbx alloys. <i>Journal of Applied Physics</i> , 2014 , 116, 123704	2.5	18
395	InGaN doping for high carrier concentration in plasma-assisted molecular beam epitaxy. <i>Physica Status Solidi C: Current Topics in Solid State Physics</i> , 2014 , 11, 381-384		11
394	Surface hole accumulation and Fermi level stabilization energy in SnTe. <i>Applied Physics Express</i> , 2014 , 7, 091201	2.4	7
393	Tellurium n-type doping of highly mismatched amorphous GaN _{1-x} As alloys in plasma-assisted molecular beam epitaxy. <i>Journal of Crystal Growth</i> , 2014 , 404, 9-13	1.6	3
392	Electronic Band Structure of GaN _x PyAs _{1-y} Highly Mismatched Alloys: Suitability for Intermediate-Band Solar Cells. <i>Physical Review Applied</i> , 2014 , 1,	4.3	60

391	. <i>IEEE Journal of Photovoltaics</i> , 2014 , 4, 196-201	3.7	18
390	Band anticrossing in ZnOSe highly mismatched alloy. <i>Applied Physics Express</i> , 2014 , 7, 071202	2.4	19
389	Fermi level stabilization and band edge energies in Cd _x Zn _{1-x} O alloys. <i>Journal of Applied Physics</i> , 2014 , 115, 233708	2.5	31
388	Surface photovoltage and modulation spectroscopy of E ₁ and E ₁ ⁺ transitions in GaNAs layers. <i>Thin Solid Films</i> , 2014 , 567, 101-104	2.2	14
387	Charge transfer and mobility enhancement at CdO/SnTe heterointerfaces. <i>Applied Physics Letters</i> , 2014 , 105, 132103	3.4	22
386	Composition and optical properties of dilute-Sb GaN _{1-x} Sb _x highly mismatched alloys grown by MBE. <i>Journal Physics D: Applied Physics</i> , 2014 , 47, 465102	3	9
385	. <i>IEEE Journal of Photovoltaics</i> , 2013 , 3, 730-736	3.7	19
384	Molecular beam epitaxial growth of ZnCdTeO epilayers for intermediate band solar cells. <i>Journal of Crystal Growth</i> , 2013 , 378, 259-262	1.6	11
383	Microstructure of GaN _{1-x} Bi _x . <i>Journal of Electronic Materials</i> , 2013 , 42, 26-32	1.9	4
382	GaNAsP: An intermediate band semiconductor grown by gas-source molecular beam epitaxy. <i>Applied Physics Letters</i> , 2013 , 102, 112105	3.4	32
381	Photocurrent induced by two-photon excitation in ZnTeO intermediate band solar cells. <i>Applied Physics Letters</i> , 2013 , 102, 052111	3.4	50
380	Crystal structure and properties of Cd _x Zn _{1-x} O alloys across the full composition range. <i>Applied Physics Letters</i> , 2013 , 102, 232103	3.4	52
379	GaN _{1-x} Sb _x highly mismatched alloys grown by low temperature molecular beam epitaxy under Ga-rich conditions. <i>Journal of Crystal Growth</i> , 2013 , 383, 95-99	1.6	13
378	Molecular beam epitaxy of highly mismatched N-rich GaN _{1-x} Sb _x and InN _{1-x} As _x alloys. <i>Journal of Vacuum Science and Technology B: Nanotechnology and Microelectronics</i> , 2013 , 31, 03C102	1.3	12
377	Development of ZnTe-Based Solar Cells. <i>Materials Science Forum</i> , 2013 , 750, 80-83	0.4	5
376	In-rich InGaN thin films: Progress on growth, compositional uniformity, and doping for device applications. <i>Journal of Vacuum Science and Technology B: Nanotechnology and Microelectronics</i> , 2013 , 31, 03C114	1.3	11
375	Microstructure of Mg doped GaNAs alloys. <i>Physica Status Solidi C: Current Topics in Solid State Physics</i> , 2013 , 10, 453-456		1
374	Highly mismatched N-rich GaN _{1-x} Sb _x films grown by low temperature molecular beam epitaxy. <i>Applied Physics Letters</i> , 2013 , 102, 102104	3.4	24

373	Local structure of amorphous GaN _{1-x} As _x semiconductor alloys across the composition range. <i>Journal of Applied Physics</i> , 2013 , 113, 243505	2.5	6
372	P-type InGaN across the entire alloy composition range. <i>Applied Physics Letters</i> , 2013 , 102, 102111	3.4	11
371	Temperature dependence of photoluminescence from InNAsSb layers: The role of localized and free carrier emission in determination of temperature dependence of energy gap. <i>Applied Physics Letters</i> , 2013 , 102, 122109	3.4	16
370	Material properties of Cd _{1-x} Mg _x O alloys synthesized by radio frequency sputtering. <i>Applied Physics Letters</i> , 2013 , 103, 041902	3.4	19
369	Contactless electroreflectance study of the Fermi level pinning on GaSb surface in n-type and p-type GaSb Van Hoof structures. <i>Journal of Applied Physics</i> , 2012 , 112, 123513	2.5	20
368	Correlations between the band structure, activation energies of electron traps, and photoluminescence in n-type GaNAs layers. <i>Applied Physics Letters</i> , 2012 , 101, 082109	3.4	18
367	Existence and removal of Cu ₂ Se second phase in coevaporated Cu ₂ ZnSnSe ₄ thin films. <i>Journal of Applied Physics</i> , 2012 , 111, 053522	2.5	74
366	Molecular beam epitaxial growth and optical properties of highly mismatched ZnTe _{1-x} O _x alloys. <i>Applied Physics Letters</i> , 2012 , 100, 011905	3.4	50
365	Ideal transparent conductors for full spectrum photovoltaics. <i>Journal of Applied Physics</i> , 2012 , 111, 123505	3.5	69
364	Two-photon excitation in an intermediate band solar cell structure. <i>Applied Physics Letters</i> , 2012 , 100, 172111	3.4	83
363	Molecular beam epitaxy of GaN _{1-x} Bi _x alloys with high bismuth content. <i>Physica Status Solidi (A) Applications and Materials Science</i> , 2012 , 209, 419-423	1.6	10
362	Structural studies of GaN _{1-x} As _x and GaN _{1-x} Bi _x alloys for solar cell applications. <i>Physica Status Solidi C: Current Topics in Solid State Physics</i> , 2012 , 9, 1586-1589		
361	Band Gap Engineering of Oxide Photoelectrodes: Characterization of ZnO _{1-x} Sex. <i>Journal of Physical Chemistry C</i> , 2012 , 116, 15281-15289	3.8	17
360	Controlling the Curie temperature in (Ga,Mn)As through location of the Fermi level within the impurity band. <i>Nature Materials</i> , 2012 , 11, 444-9	2.7	148
359	Wurtzite-to Amorphous-to Cubic Phase Transition of GaN _{1-x} As _x Alloys with Increasing as Content. <i>Solid State Phenomena</i> , 2012 , 186, 74-77	0.4	1
358	Red-green luminescence in indium gallium nitride alloys investigated by high pressure optical spectroscopy. <i>Applied Physics Letters</i> , 2012 , 100, 162103	3.4	13
357	Temperature dependence of E ₀ and E ₀ + β 0 transitions in In _{0.53} Ga _{0.47} Bi _x As _{1-x} alloys studied by photoreflectance. <i>Journal of Applied Physics</i> , 2012 , 112, 113508	2.5	14
356	Tuning structural, electrical, and optical properties of oxide alloys: ZnO _{1-x} Sex. <i>Journal of Applied Physics</i> , 2012 , 111, 113505	2.5	9

355	Band Gap Variation of CdInSe and CdZnS Fabricated by High Throughput Combinatorial Growth Technique 2011 ,			1
354	Demonstration of ZnTe _{1-x} O _x Intermediate Band Solar Cell. <i>Japanese Journal of Applied Physics</i> , 2011 , 50, 082304	1.4		15
353	Engineering the electronic band structure for multiband solar cells. <i>Physical Review Letters</i> , 2011 , 106, 028701	7.4		225
352	Thermal stability of amorphous GaN _{1-x} As _x alloys. <i>Applied Physics Letters</i> , 2011 , 98, 161902	3.4		7
351	Growth by molecular beam epitaxy of amorphous and crystalline GaNAs alloys with band gaps from 3.4 to 0.8 eV for solar energy conversion devices. <i>Journal of Crystal Growth</i> , 2011 , 323, 60-63	1.6		10
350	GaNAs alloys over the whole composition range grown on crystalline and amorphous substrates. <i>Physica Status Solidi C: Current Topics in Solid State Physics</i> , 2011 , 8, 2503-2505			7
349	Photovoltaic action from In _x Ga _{1-x} N p-n junctions with x > 0.2 grown on silicon. <i>Physica Status Solidi C: Current Topics in Solid State Physics</i> , 2011 , 8, 2466-2468			8
348	Mechanisms of Schottky Barrier Control on n-Type Germanium Using Ge ₃ N ₄ Interlayers. <i>Journal of the Electrochemical Society</i> , 2011 , 158, H358	3.9		35
347	Electronic structure of CdO studied by soft X-ray spectroscopy. <i>Journal of Electron Spectroscopy and Related Phenomena</i> , 2011 , 184, 249-253	1.7		22
346	Preparation of high transmittance ZnO:Al film by pulsed filtered cathodic arc technology and rapid thermal annealing. <i>Applied Surface Science</i> , 2011 , 257, 7019-7022	6.7		8
345	Determination of effective mass in InN by high-field oscillatory magnetoabsorption spectroscopy. <i>Physical Review B</i> , 2011 , 83,	3.3		33
344	Decoupling single nanowire mobilities limited by surface scattering and bulk impurity scattering. <i>Journal of Applied Physics</i> , 2011 , 110, 033705	2.5		11
343	Mg doped InN and confirmation of free holes in InN. <i>Applied Physics Letters</i> , 2011 , 98, 042104	3.4		41
342	Doping of GaN _{1-x} As _x with high As content. <i>Journal of Applied Physics</i> , 2011 , 110, 093702	2.5		4
341	Electrical and optical properties of p-type InN. <i>Journal of Applied Physics</i> , 2011 , 110, 123707	2.5		19
340	Effects of point defects on thermal and thermoelectric properties of InN. <i>Applied Physics Letters</i> , 2011 , 98, 012108	3.4		36
339	Growth and transport properties of p-type GaN _{1-x} Bi _x alloys. <i>Journal of Materials Research</i> , 2011 , 26, 2887-2894			15
338	Electrical and optical characterization of n-InAsSb/n-GaSb heterojunctions. <i>Journal of Applied Physics</i> , 2010 , 107, 014512	2.5		6

337	GaN _{1-x} Bix: Extremely mismatched semiconductor alloys. <i>Applied Physics Letters</i> , 2010 , 97, 141919	3.4	31
336	Molecular beam epitaxy of GaNAs alloys with high As content for potential photoanode applications in hydrogen production. <i>Journal of Vacuum Science and Technology B: Nanotechnology and Microelectronics</i> , 2010 , 28, C3B12-C3B16	1.3	13
335	Fermi level stabilization energy in cadmium oxide. <i>Journal of Applied Physics</i> , 2010 , 107, 113706	2.5	54
334	Full multiple scattering analysis of XANES at the Cd L3 and O K edges in CdO films combined with a soft-x-ray emission investigation. <i>Physical Review B</i> , 2010 , 82,	3.3	36
333	Electronic structure of Ga _{1-x} MnxAs analyzed according to hole-concentration-dependent measurements. <i>Physical Review B</i> , 2010 , 81,	3.3	43
332	Hole transport and photoluminescence in Mg-doped InN. <i>Journal of Applied Physics</i> , 2010 , 107, 113712	2.5	62
331	Progress on III-nitride/silicon hybrid multijunction solar cells 2010 ,		3
330	Electron cyclotron effective mass in indium nitride. <i>Applied Physics Letters</i> , 2010 , 96, 052117	3.4	35
329	Demonstration of homojunction ZnTe solar cells. <i>Journal of Applied Physics</i> , 2010 , 108, 024502	2.5	33
328	Low gap amorphous GaN _{1-x} Asx alloys grown on glass substrate. <i>Applied Physics Letters</i> , 2010 , 97, 101906	3.4	16
327	Band structure engineering of ZnO 1-x Se x alloys 2010 ,		1
326	Band structure engineering of ZnO _{1-x} Sex alloys. <i>Applied Physics Letters</i> , 2010 , 97, 022104	3.4	50
325	Defect redistribution in postirradiation rapid-thermal-annealed InN. <i>Physical Review B</i> , 2010 , 82,	3.3	10
324	Finite element simulations of compositionally graded InGaN solar cells. <i>Solar Energy Materials and Solar Cells</i> , 2010 , 94, 478-483	6.4	145
323	Irradiation-induced defects in InN and GaN studied with positron annihilation. <i>Physica Status Solidi (A) Applications and Materials Science</i> , 2010 , 207, 1087-1090	1.6	7
322	High quality In _x Ga _{1-x} N thin films with x > 0.2 grown on silicon. <i>Physica Status Solidi (B): Basic Research</i> , 2010 , 247, 1747-1749	1.3	13
321	Non-equilibrium GaNAs alloys with band gap ranging from 0.8-3.4 eV. <i>Physica Status Solidi C: Current Topics in Solid State Physics</i> , 2010 , 7, 1847-1849		14
320	Hall mobilities in GaN _x As _{1-x} . <i>Physica Status Solidi C: Current Topics in Solid State Physics</i> , 2010 , 7, 1890-1893		2

319	Highly mismatched crystalline and amorphous GaN _{1-x} As _x alloys in the whole composition range. <i>Journal of Applied Physics</i> , 2009 , 106, 103709	2.5	54
318	Numerical simulations of novel InGaN solar cells 2009 ,		2
317	MBE GROWTH AND CHARACTERIZATION OF Mg-DOPED III-NITRIDES ON SAPPHIRE. <i>Selected Topics in Electronics and Systems</i> , 2009 , 113-119	0	
316	Properties of native point defects in In _{1-x} Al _x N alloys. <i>Journal Physics D: Applied Physics</i> , 2009 , 42, 0954063		2
315	Determining surface Fermi level pinning position of InN nanowires using electrolyte gating. <i>Applied Physics Letters</i> , 2009 , 95, 173114	3.4	16
314	MBE GROWTH AND CHARACTERIZATION OF Mg-DOPED III-NITRIDES ON SAPPHIRE. <i>International Journal of High Speed Electronics and Systems</i> , 2009 , 19, 113-119	0.5	
313	Growth by Molecular Beam Epitaxy of GaNAs Alloys with High As Content for Potential Photoanode Applications in Hydrogen Production. <i>Materials Research Society Symposia Proceedings</i> , 2009 , 1167, 7		
312	Strain relaxation of CdTe films growing on lattice-mismatched substrates. <i>Applied Physics A: Materials Science and Processing</i> , 2009 , 96, 379-384	2.6	8
311	Highly luminescent In _x Ga _{1-x} N thin films grown over the entire composition range by energetic neutral atom beam lithography & epitaxy (ENABLE). <i>Physica Status Solidi C: Current Topics in Solid State Physics</i> , 2009 , 6, S409-S412		4
310	Optical properties of ion beam synthesized nitrogen-rich GaN _{1-x} As _x . <i>Physica Status Solidi C: Current Topics in Solid State Physics</i> , 2009 , 6, S796-S799		
309	Electrical properties of InGaN-Si heterojunctions. <i>Physica Status Solidi C: Current Topics in Solid State Physics</i> , 2009 , 6, S413-S416		24
308	Stacking faults and phase changes in Mg-doped InGaN grown on Si. <i>Physica Status Solidi C: Current Topics in Solid State Physics</i> , 2009 , 6, S421-S424		4
307	Electrical and electrothermal transport in InN: The roles of defects. <i>Physica B: Condensed Matter</i> , 2009 , 404, 4862-4865	2.8	10
306	Molecular beam epitaxy of crystalline and amorphous GaN layers with high As content. <i>Journal of Crystal Growth</i> , 2009 , 311, 3417-3422	1.6	19
305	Temperature dependence of the band gap of ZnSe _{1-x} O _x . <i>Applied Physics Letters</i> , 2009 , 95, 151907	3.4	31
304	Demonstration of a III-Nitride/Silicon Tandem Solar Cell. <i>Applied Physics Express</i> , 2009 , 2, 122202	2.4	54
303	Chapter 3 Fermi Level Effects on Mn Incorporation in III-Mn-V Ferromagnetic Semiconductors. <i>Semiconductors and Semimetals</i> , 2008 , 82, 89-133	0.6	1
302	InGaN/Si heterojunction tandem solar cells. <i>Conference Record of the IEEE Photovoltaic Specialists Conference</i> , 2008 ,		3

301	Experimental and theoretical studies on gadolinium doping in ZnTe. <i>Journal of Applied Physics</i> , 2008 , 103, 023711	2.5	6
300	Electronic Band Structure of Highly Mismatched Semiconductor Alloys 2008 , 65-89		3
299	Formation of Mn-derived impurity band in III-Mn-V alloys by valence band anticrossing. <i>Physical Review B</i> , 2008 , 78,	3.3	41
298	Modeling of InGaN/Si tandem solar cells. <i>Journal of Applied Physics</i> , 2008 , 104, 024507	2.5	126
297	Band gap bowing parameter of In _{1-x} Al _x N. <i>Journal of Applied Physics</i> , 2008 , 104, 123501	2.5	62
296	Composition dependence of the hole mobility in GaSbAs _{1-x} . <i>Applied Physics Letters</i> , 2008 , 92, 162105	3.4	3
295	Probing and modulating surface electron accumulation in InN by the electrolyte gated Hall effect. <i>Applied Physics Letters</i> , 2008 , 93, 262105	3.4	29
294	InGaN Thin Films Grown by ENABLE and MBE Techniques on Silicon Substrates. <i>Materials Research Society Symposia Proceedings</i> , 2008 , 1068, 1		8
293	Properties of Ga _{1-x} Mn _x As with high x (>0.1). <i>Journal of Applied Physics</i> , 2008 , 103, 07D136	2.5	19
292	Effects of donor doping on Ga _{1-x} Mn _x As. <i>Applied Physics Letters</i> , 2008 , 93, 262505	3.4	16
291	Band anticrossing in highly mismatched Sn _x Ge _{1-x} semiconducting alloys. <i>Physical Review B</i> , 2008 , 77,	3.3	59
290	Optimum nitride concentration in multiband III-N _x alloys for high efficiency ideal solar cells. <i>Applied Physics Letters</i> , 2008 , 93, 174109	3.4	17
289	High efficiency InAlN-based solar cells. <i>Conference Record of the IEEE Photovoltaic Specialists Conference</i> , 2008 ,		2
288	Characterization of Mg-doped InGaN and InAlN alloys grown by MBE for solar applications. <i>Conference Record of the IEEE Photovoltaic Specialists Conference</i> , 2008 ,		2
287	Metal-insulator transition by isovalent anion substitution in Ga _{1-x} Mn _x As: implications to ferromagnetism. <i>Physical Review Letters</i> , 2008 , 101, 087203	7.4	32
286	Low-temperature grown compositionally graded InGaN films. <i>Physica Status Solidi C: Current Topics in Solid State Physics</i> , 2008 , 5, 1866-1869		16
285	Mg-doped InN and InGaN [Photoluminescence, capacitance-voltage and thermopower measurements. <i>Physica Status Solidi (B): Basic Research</i> , 2008 , 245, 873-877	1.3	53
284	Epitaxial growth of CdSexTe _{1-x} thin films on Si(100) by molecular beam epitaxy using lattice mismatch graded structures. <i>Journal of Crystal Growth</i> , 2008 , 310, 1081-1087	1.6	13

283	Single crystal growth and properties of β phase in the $\text{CuInSe}_2+2\text{CdS} \rightarrow \text{CuInS}_2+2\text{CdSe}$ reciprocal system. <i>Solar Energy Materials and Solar Cells</i> , 2008 , 92, 1495-1499	6.4	15
282	Energetic Beam Synthesis of Dilute Nitrides and Related Alloys 2008 , 1-34		
281	Effects of quantum confinement on the doping limit of semiconductor nanowires. <i>Nano Letters</i> , 2007 , 7, 1186-90	11.5	59
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